

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









TSM4459

30V P-Channel MOSFET



SOP-8

Pin Definition:



Source
 Source
 Drain
 Drain
 Drain

4. Gate 5. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)	
-30	5.2 @ V _{GS} = -10V	4-7	
	9.5 @ V _{GS} = -4.5V	-17	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

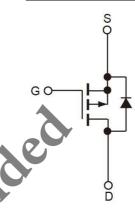
- DC-DC Converter
- Battery Power System

Ordering Information

Part No.	Package	Packing
TSM4459CS RLG	SOP-8	2.5Kpcs / 13" Reel

Note: "G" denote for Halogen Free Product

Block Diagram



P-Channel MOSFET

Absolute Maximum Rating (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	-30	V	
Gate-Source Voltage	V_{GS}	±20	V	
Continuous Drain Current	- I _D -	-17	А	
Continuous Drain Current		-13.6		
Pulsed Drain Current	I _{DM}	-68	Α	
Mayiroum Payar Dissination total	Б	2.5	W	
Maximum Power Dissipation $T_A = 25^{\circ}C$ $T_A = 70^{\circ}C$	P_{D}	1.6		
Operating Junction Temperature	T_J	+150	°C	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Ambient Thermal Resistance Note a.	R⊖ _{JA}	50	°C/W

Notes:

a. The Device Surface Mounted on 1inch² FR4 Board with 2oz copper.

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Electrical Specifications (T_A = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1		-3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V$	I _{DSS}			-1.0	μΑ
Drain-Source On-State Resistance	$V_{GS} = -10V, I_{D} = -9A$	D		4	5.2	mO
Dialii-Source Oil-State nesistance	$V_{GS} = -4.5V, I_{D} = -9A$	$R_{DS(ON)}$		7	9.5	mΩ
Diode Forward Voltage	$I_S = -18A, V_{GS} = 0V$	$V_{\sf SD}$		8.0		V
Dynamic						
Total Gate Charge	\/ Q4\/ L 17A	Q_g	_2	78.4		
Gate-Source Charge	$V_{DS} = -24V, I_D = -17A,$ $V_{GS} = -4.5V$	Q _{gs}	0	25.1		nC
Gate-Drain Charge	V _{GS} = -4.5 V	Q _{gd}		38.7		
Gate Resistance	f = 1.0MHz	R		2.88		Ω
Input Capacitance	\\ 45\\\\\ 0\\	S_{iss}		6205		
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ $f = 1.0MHz$	oss	1	963		рF
Reverse Transfer Capacitance	1 = 1.0IVIM2	C_{rss}	1	330		
Switching						
Turn-On Delay Time	$V_{DD} = -15V, R = 15\Omega,$ $V_{GEN} = -10V,$ $R_{G} = 4.7\Omega$	t _{d(on)}		75.2		
Turn-On Rise Time		t _r		33.8		20
Turn-Off Delay Time		t _{d(off)}	-	275		nS
Turn-Off Fall Time	ng = 4.772	t _f		92.1		

Notes:

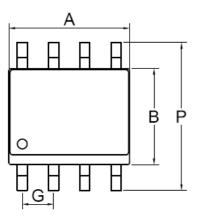
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Notes: a. pulse test: PW ≤300μS, duty cycle ≤2%

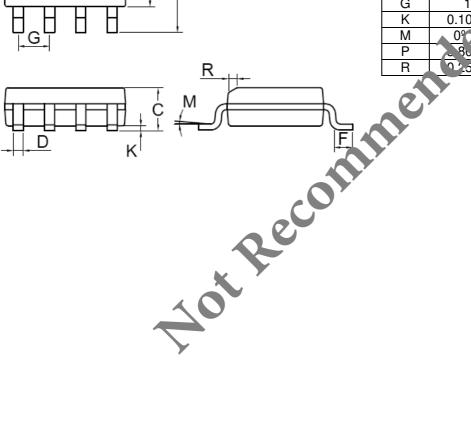




SOP-8 Mechanical Drawing



SOP-8 DIMENSION						
DIM	MILLIMETERS		INCHES			
DIIVI	MIN	MAX	MIN	MAX.		
Α	4.80	5.00	0.189	0.196		
В	3.80	4.00	0.150	0.157		
С	1.35	1.75	0.054	0.068		
D	0.35	0.49	0.014	0.019		
F	0.40	1.25	0.016	0.049		
G	1.2 BSC		0.05BSC			
K	0.10	0.25	0.004	0.009		
М	09	7º	0₀	7º		
Р	ر 8	6.20	0.229	0.244		
R	7.5	0.50	0.010	0.019		



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TSM4459

30V P-Channel MOSFET

Aot Recommended.

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